VSKY20401608-G4-08-FS

Silicon Schottky Barrier Diode

Features

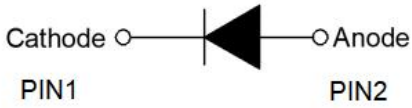
- Small Surface Mounting Type
- Ideal for Automated Placement
- Ultrafast Reverse Recovery Time
- Low Power Losses, High Efficiency
- Low Forward Voltage Drop
- High Surge Capability
- RoHS Compliant

Applications

- Low Voltage
- High-Frequency Inverters
- Free Wheeling
- Switching circuit



DFN1608-2L



Mechanical data

- Package: DFN1608-2L
- Lead Finish:Matte Tin
- Case Material: “Green” Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Tape Reel :3000pcs

Marking



S24= Marking Code

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Absolute Maximum Ratings (T=25ºC, RH=45%-75%, unless otherwise noted)

Parameters	Symbol	Limit	Unit
Reverse Voltage (Repetitive Peak)	V_{RRM}	40	V
Reverse Voltage (RMS)	$V_{R(RMS)}$	32	V
DC Reverse Voltage	V_R	40	V
Average Rectified Output Current	I_O	2	A
Non-repetitive Peak Forward Surge Current@t=8.3ms	I_{FSM}	20	A
Thermal Resistance Junction to Ambient （Typ）	$R_{\theta JA}$	80	℃/W
Junction Temperature	T_J	-55 to +150	℃
Storage Temperature	T_{STG}	-55 to +150	℃

Electrical Characteristics (T=25ºC, RH=45%-75%, unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Max	Unit
Reverse Breakdown Voltage	V_{BR}	I_R = 0.5mA	40		V
Reverse Leakage Current	I_R	V_R = 4V		15	uA
		V_R = 40V		100	uA
Forward Voltage	V_F	I_F = 1A		0.47	V
		I_F = 2A		0.55	

Typical Characteristics

FIG1：Io-TL Curve

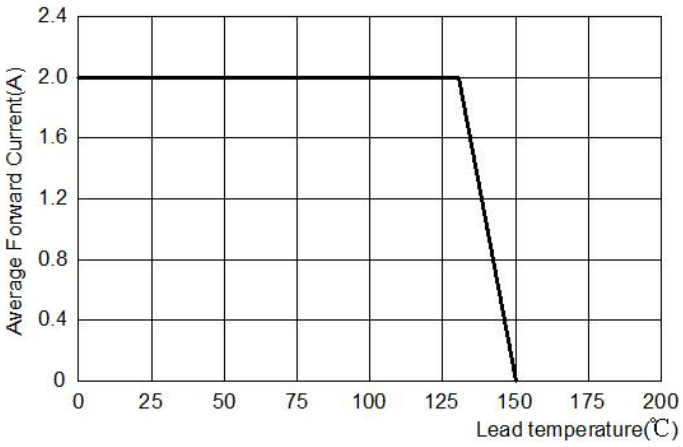


FIG2：Surge Forward Current Capability

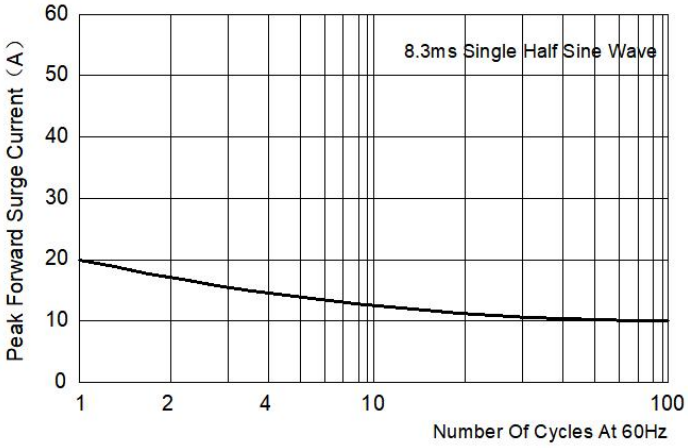


FIG3：Typcal Reverse Characteristics

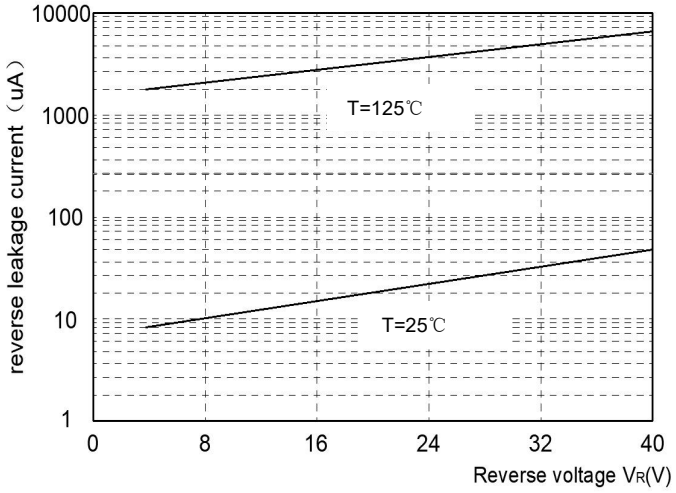
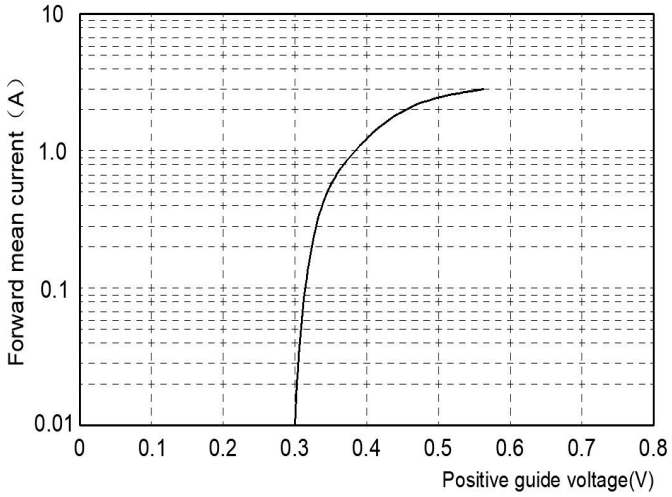
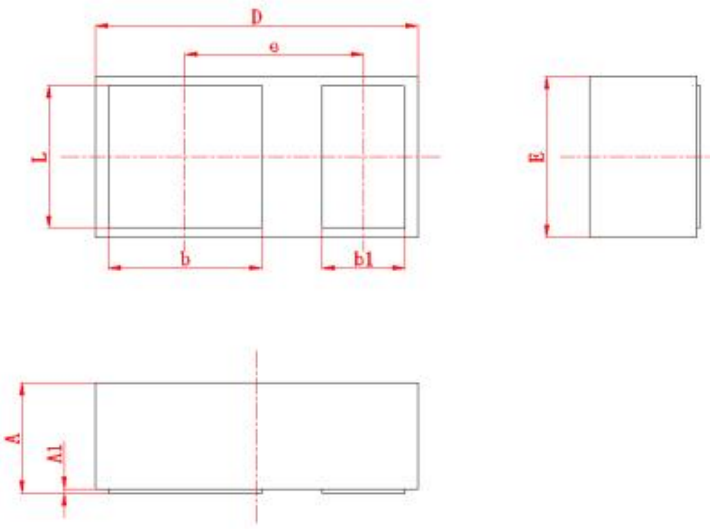


FIG4: Typcal Forward Characteristics

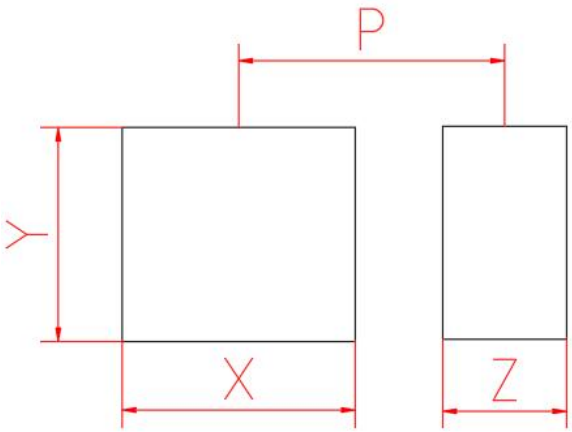


Package mechanical data



Symbol	Dimension in Millimeters	
	min	max
A	0.50	0.6
A1	0	0.05
D	1.5	1.7
E	0.75	0.85
e	(0.89)	
b	0.71	0.81
b1	0.36	0.46
L	0.66	0.76

Suggested Land Pattern for PCB



Symbol	Dimension in Millimeters
	typ
X	0.95
Y	0.85
Z	0.6
P	0.9